

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

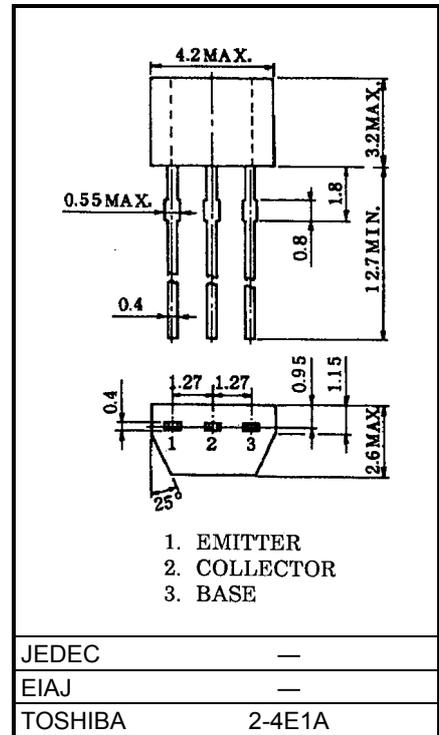
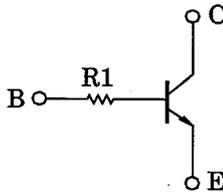
RN1241, RN1242, RN1243, RN1244

For Muting and Switching Applications

Unit: mm

- High emitter-base voltage
: $V_{EBO} = 25\text{v}$ (min)
- High reverse hfe
: reverse $h_{FE} = 150$ (typ.) ($V_{CE} = -2\text{V}$, $I_C = -4\text{ma}$)
- Low on resistance
: $R_{ON} = 1\Omega$ (typ.) ($I_B = 5\text{mA}$)
- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process

Equivalent Circuit



Weight: 0.13g

Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V_{CEO}	20	V
Emitter-base voltage	V_{EBO}	25	V
Collector current	I_C	300	mA
Collector power dissipation	P_C	300	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55~150	$^\circ\text{C}$

Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current		I_{CBO}	—	$V_{CB} = 50V, I_E = 0$	—	—	0.1	μA
Emitter cut-off current		I_{EBO}	—	$V_{EB} = 25V, I_C = 0$	—	—	0.1	μA
DC current gain		h_{FE} (Note)	—	$V_{CE} = 2V, I_C = 4mA$	200	—	1200	—
Collector-emitter saturation voltage		$V_{CE(sat)}$	—	$I_C = 30mA, I_B = 3mA$	—	—	0.1	V
Transition frequency		f_T	—	$V_{CE} = 6V, I_C = 4mA$	—	30	—	MHz
Collector output capacitance		C_{ob}	—	$V_{CB} = 10V, I_E = 0, f = 1MHz$	—	4.8	—	pF
Input resistor	RN1241	R1	—	—	3.9	5.6	7.3	k Ω
	RN1242		—		7	10	13	
	RN1243		—		15.4	22	28.6	
	RN1244		—		1.54	2.2	2.86	

Note: hEE Classification A: 200~700 B: 350~1200

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